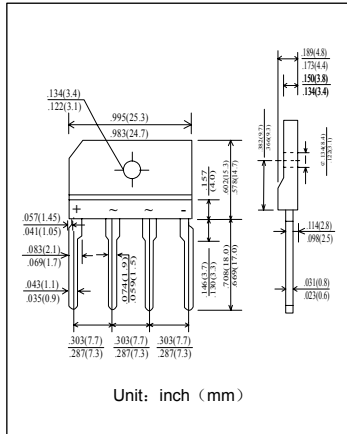




Single-phase Silicon Bridge Rectifier

D4SB20 THRU D4SB80

Reverse Voltage 200 to 800 V
Forward Current 4.0A



特征 Features

- 低的反向漏电流 Low reverse leakage
- 较强的正向浪涌承受能力 High forward surge capability
- 浪涌承受能力: 170 A Surge overload rating: 170 Amperes peak

机械数据 Mechanical Data

- 封装: 塑料封装 Case: Molded Plastic
- 极性: 标记模压或印于本体 Polarity: Symbols molded or marked on body
- 安装位置: 任意 Mounting Position: Any
- 重量: 4.6 克 Weight: 4.6 Grams

极限值和温度特性 TA = 25°C 除非另有规定。

Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

	符号 Symbols	D4SB20	D4SB40	D4SB60	D4SB80	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	V_{RRM}	200	400	600	800	V
最大均方根电压 Maximum RMS voltage	V_{RMS}	140	280	420	560	V
最大直流阻断电压 Maximum DC blocking voltage	V_{DC}	200	400	600	800	V
最大正向平均整流电流 加散热片 $T_c = 108^\circ C$ Maximum average forward rectified current 无散热片 $T_a = 25^\circ C$	$I_{F(AV)}$	4.0				A
		2.3				
峰值正向浪涌电流 8.3ms 单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	I_{FSM}	150				A
最大反向峰值电流 @ $T_A = 75^\circ C$ Maximum peak reverse current full cycle	$I_{R(AV)}$	30				μA
典型热阻 Typical thermal resistance	$R_{\theta JA}$	6				$^\circ C/W$
工作结温和存储温度 Operating junction and storage temperature range	T_j, T_{STG}	-50 --- +150				$^\circ C$

电特性 TA = 25°C 除非另有规定。

Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

	符号 Symbols	D4SB20	D4SB40	D4SB60	D4SB80	单位 Unit
最大正向电压 $I_F = 2.0A$ Maximum forward voltage	V_F	0.95				V
最大反向电流 $T_A = 25^\circ C$ Maximum reverse current	I_R	10				μA
典型结电容 $V_R = 4.0V, f = 1MHz$ Type junction capacitance	C_j	40				pF



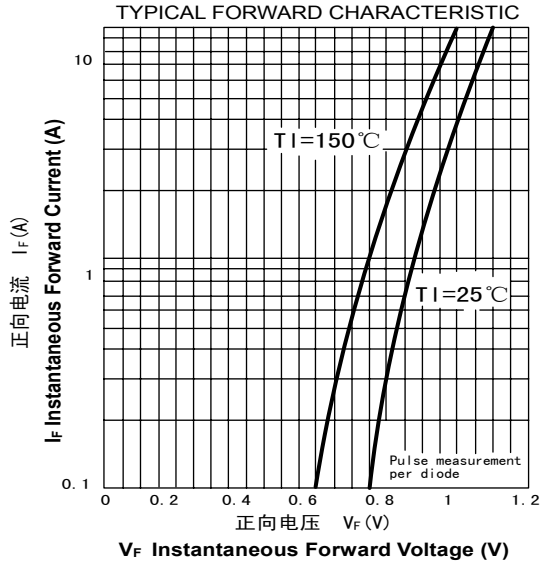
Single-phase Silicon Bridge Rectifier

D4SB20 THRU D4SB80

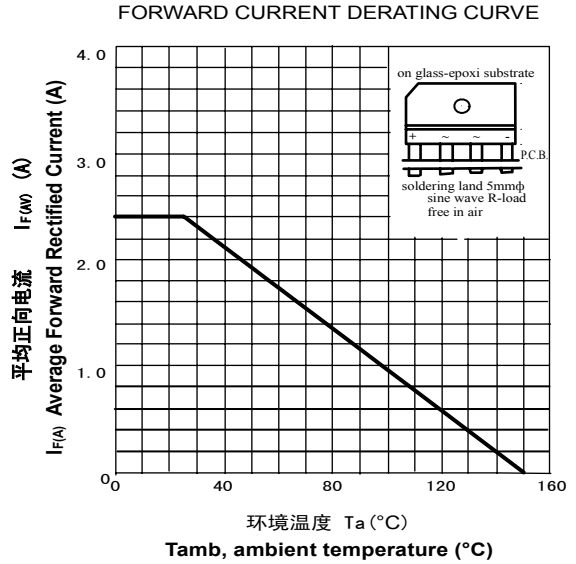
Reverse Voltage 200 to 800 V
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Characteristic Curves

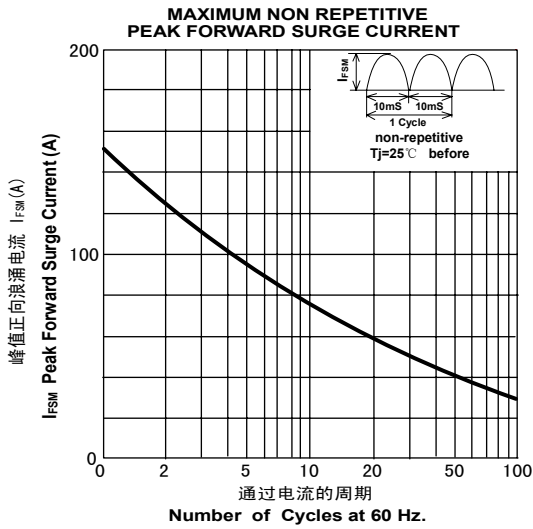
正向特性曲线 (典型值)



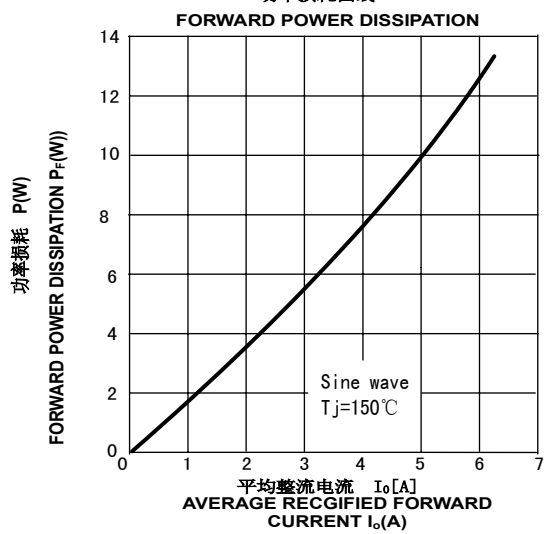
正向电流降额曲线



浪涌特性曲线 (最大值)



功率损耗曲线



正向电流降额曲线

